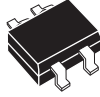


CBRHDSH1-40L  
 HIGH DENSITY  
 1.0 AMP DUAL IN LINE  
 LOW  $V_F$   
 SCHOTTKY BRIDGE RECTIFIER

**HD**BRIDGE



HD DIP CASE

**Central**<sup>TM</sup>  
 Semiconductor Corp.

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CBRHDSH1-40L type is a full wave bridge rectifier mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

**MARKING CODE: CSH1**

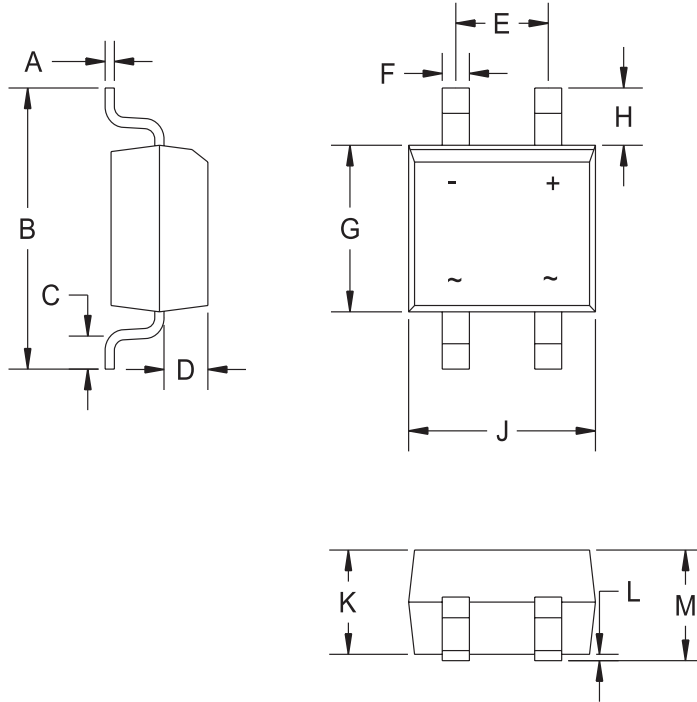
**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	$V_{RRM}$	40	V
DC Blocking Voltage	$V_R$	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Average Forward Current	$I_O$	1.0	A
Peak Forward Surge Current	$I_{FSM}$	20	A
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS PER DIODE:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
$I_R$	$V_R=40\text{V}$	20	50	$\mu\text{A}$
$V_F$	$I_F=500\text{mA}$	360	380	mV
$V_F$	$I_F=1.0\text{A}$	390	440	mV
$C_J$	$V_R=4.0\text{V}, f=1.0\text{MHz}$	150		pF

HD DIP CASE - MECHANICAL OUTLINE



R1

MARKING CODE: CSH1

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.006	0.014	0.15	0.35
B	-	0.276	-	7.00
C	0.028	0.043	0.70	1.10
D	0.035	0.051	0.90	1.30
E	0.091	0.106	2.30	2.70
F	0.020	0.031	0.50	0.80
G	0.142	0.157	3.60	4.00
H	0.051	0.067	1.30	1.70
J	0.177	0.193	4.50	4.90
K	0.091	0.106	2.30	2.70
L	-	0.008	-	0.20
M	-	0.118	-	3.00

HD DIP (REV: R1)

R0 (6-June 2005)